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(54) Title: SOLID-STATE GAS SENSORS AND COM (57) Abstract Compounds of the formula (MWO ₄) _x (ZO ₂) _{1-x} , where			Zn, and Z is selected from

Compounds of the formula $(MWO_4)_x(ZO_2)_{1-x}$, where M is selected from Mg, Mn, Fe, Co, Ni, and Cu and/or Zn, and Z is selected from Sn and Ti, where 0 < x < 1 are wolframite—based solid solutions which find utility as solid-state gas sensors for sensing carbon—monoxide, ammonia, methane.

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Solid-State Gas Sensors And Compounds Therefor

This invention relates to wolframite-based solid solution compounds, gas sensors made therefrom, and the detection and measuring of the concentration of various gases with such sensors.

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Semiconducting oxide gas sensors have been primarily used for the detection of combustible gases such as carbon monoxide and hydrocarbons. The response mechanism, described in detail elsewhere (eg [1-2]), relies on the bulk resistance of porous solids mainly depending on ionosorbed oxygen species acting as electron traps. Thus, the interaction of a gas with these surface species results in a change in their surface concentration, which consequently affects the solid resistance. Systematic cation substitution in solid-solution materials as a way of understanding the gas response mechanism linked to the surface chemistry has been previously studied for $Cr_{2-y}Ti_yO_{2+x}$ [3,4], $Ba_6Fe_xNb_{10-x}O_{30}$ [5], $(CrNbO_4)_x(Sn_{1-y}Sb_yO_2)_{1-x}$ [6], and $FeNbO_4$ -CrNbO₄-TiO₂ [7] and the effects of stoichiometry, microstructure, gas concentration gradients, and surface segregation on gas sensitivity have been observed. Analysis of the variation of conductivity with reactive gas concentration implies that the surface trap state is formally O_{ads}^{2-} . We have recently shown that this state can be described as an oxygen molecule adsorbed on a surface oxygen vacancy - reduced cation complex [8]. Oxides can be classified according to the sign of resistance change to reducing gases, as 'n' (resistance decrease) or 'p' (resistance increase). A model which rationalises the effects of bulk donor doping has been developed [9] which predicts a switch from n- to p-type response and conductance minimum at some value of the surface acceptor state density dependent on the bulk donor density.

Previous work [3, 8] has considered solid solution series with transition metal ions in high oxidation states. The present work considers solid solution series with transition metal ions in low oxidation states. The divalent transition metal tungstates, AWO₄ (A = Mn, Fe, Co, Ni, Cu, and Zn)., also referred to as NiWO₄-type tungstates, are members of a large family of structurally related compounds with small cations which crystallize with the wolframite structure [10]. The structure is monoclinic with Z = 2 and space group P2/c (C_{2h}^4). For pure FeWO₄ (feberite), a = 4.730 \mathring{A} , b = 5.703 \mathring{A} , c = 4.952 \mathring{A} , and $\mathring{\beta} = 90^{\circ}05^{\circ}$ [11]. The structure consists of a hexagonal close-packed oxygen array in which one-half of the octahedral holes are occupied. The cation

distribution in the octahedral interstices give rise to zigzag chains of skew-edge linked octahedra extending along the c-axis, and in any single chain there is only one type of cation. The zigzag chains are arranged in alternating layers, perpendicular to the a direction. Between layers, the chains are connected by corner-sharing octahedra so that no chain of one type of cation is linked to another of the same cation. The structural similarity between wolframite and rutile implied the possibility of solid solution series of SnO₂ or TiO₂ with the transition metal tungstates, which would allow the systematic investigation of effects of d-electron population on gas sensitivity. Such a study would give a further test of the general model for gas response given earlier and, by comparison of the effects of different gases, might reveal particular effects attributable to some specific chemistry of the surface. The present paper reports this study.

Tungstates have been investigated for other technological applications. Single crystals of zinc tungstate have, in particular, received much attention because of their potential technological significance in applications such as scintillation detectors, photoanodes and masers. Several studies have reported a wide range of properties of these materials. Watterich *et al* [12] have investigated the properties of paramagnetic defects in ZnWO₄ single-crystals induced by electron-irradiation. Intrinsic paramagnetic defects in undoped zinc tungstate crystals have been observed by ESR after electron irradiation. The only hole-type defect was attributed to a hole trapped at an O²⁻ ion near a zinc vacancy. Two electron-excess centers were due to a single electron trapped at an oxygen vacancy where the defects differed in the oxygen vacancy position. Ti(III) centers in reduced ZnWO₄-Ti single crystals were also examined [13] by ESR methods which resulted in the characterization of a new Ti³⁺ centre expressed as [Ti³⁺-H].

The d.c. electrical conductivity and thermoelectric power of CuWO₄ have been measured [14] in the temperature range 300 to 700 K on single crystals and on polycrystalline pellets. It has been found that CuWO₄ is an n-type semiconductor. The intrinsic nature of the compound is observed above 455 K with an activation energy of 1.06 eV for polycrystalline pellets. Other authors have reported that CuWO₄ can be

considered as an intrinsic semiconductor with a band gap of 1.52 eV [15].

Measurements of a.c. and d.c. electrical conductivity of nickel tungstate indicated [16] that NiWO₄ has a band gap of 2.10 eV. The conduction mechanism above 500 K (with high resistivity $\approx 10^9 \ \Omega$.cm and $E_a = 1.5 \ eV$) was proposed as an electron transfer from one Ni²⁺ to an adjacent Ni²⁺ ion. Such a transfer would lead to the formation of Ni³⁺ ions (Ni²⁺ + Ni²⁺ \rightarrow Ni³⁺ + Ni⁺) which would require high energy as both Ni³⁺ and Ni⁺ ions are less stable than Ni²⁺.

Conductivity measurement in CoWO₄ single crystals showed [17] that cobalt tungstate is a p-type semiconductor. The solid exhibited extrinsic behaviour up to 750K ($E_A = 0.64 \text{ eV}$) and intrinsic behaviour above this temperature ($E_A = 1.4 \text{ eV}$) implying a band gap of 2.80 eV.

Single crystals and polycrystalline samples of FeWO₄ were prepared and characterized by Sieber et al. [18]. From high temperature paramagnetic data, the presence of high spin state iron(II) $3d^6$ was confirmed. Qualitative Seebeck measurements indicated p-type conductivity, and the room temperature resistivity of single crystals was $\approx 100\Omega$ cm with an activation energy of 0.16 eV. The p-type conductivity was interpreted as caused by a small amount of iron(III) being present, due to the formation of a small quantity of Fe₂WO₆, which is able to form a solid solution with FeWO₄. Another study by Bharati *et al.* [19] suggested that the solid exhibited extrinsic behaviour up to 900K ($E_A = 0.27$ eV) characteristic of conductivity governed by impurities or defects, and intrinsic behaviour above this temperature ($E_A = 0.64$ eV).

Electrical conductivity of a single crystal of MnWO₄ in the temperature range 300-1200K has been reported [20]. It was found that the dominant charge carriers are holes (p-type material) over the entire temperature range studied. A break in the Arrhenius plot (σ vs 1/T) occurred around 600K. The activation energy below and above this break temperature was estimated as 0.53 and 0.57 eV respectively.

The A(II)B(VI)O₄ tungstates are potential compounds for use as photoelectrodes for

the photoassisted decomposition of water using sunlight, and as gas detectors because these materials have the possibility of being either p-type or n-type semiconductors. P-type behaviour could be observed when a small amount of one of the transition metals is oxidized, e.g. the introduction of a small amount of iron (III) as Fe₂WO₆ in iron (II) tungstate. In addition, n-type behaviour might be produced when one of the metals in the structure is reduced to a lower oxidation state, e.g. the reduction of W(VI) to W(V). Thus, the ABO₄ tungstates have potential use as either photocathodes or photoanodes in the photoassisted decomposition of water [21,22]. Some metal tungstates and their composites with carbonates have also been investigated for application to semiconductor-type sensors capable of detecting nitrogen oxides at elevated temperature [23].

We have synthesised a range of new wolframite-based oxides and have discovered that they have utility as gas sensitive resistors. They have particular effect for the sensing of carbon monoxide, ammonia, and methane.

The invention is defined by the claims hereinafter.

These new oxides have the formula $(MWO_4)_x(ZO_2)_{1-x}$ where M is selected from Mg, Mn, Fe, Co, Ni, Cu, and/or Zn, and Z is selected from Sn and Ti. M can be more than one of Mn, Fe, Co, Ni, Cu, and Zn, and Z can be Sn and Ti in the same compound.

The Wolframites, MWO₄, can be prepared from aqueous metal nitrate solutions by the addition of ammonium tungstate solution. They are miscible in the solid state with SnO₂ and TiO₂. The new oxides can therefore be prepared by solid state synthesis from mixed powders of the tungstate with SnO₂ or TiO₂, generally with calcination at a temperature of 1000-1300°C.

The sintered oxides can be employed as solid state gas sensors, for example as a thick film on an inert substrate and employing high temperature stabilisation, as described in our earlier WO 95/04926. Typically the film is up to 300 microns thick.

Preferred features of the invention will now be described, by way of

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example, with reference to the accompanying drawings in which:-

Figure 1 is a graph showing the resistance against time of an (FeWO₄)_{0.1}(SnO₂)_{0.9} sensor upon exposure to 1% CO and CH₄ in air at 420 and 510°C;

Figure 2 is a graph depicting the resistivity of various oxides of the invention at 400°C with varying TiO₂ and SnO₂ concentration;

Figure 3 shows the conductance activation energy for various oxides of the invention for the temperature range 400-500°C with varying TiO₂ and SnO₂ concentration;

Figure 4 shows the sensitivity, as defined below, Sco of oxides of the invention to 1% carbon monoxide in dry air, at 400°C, with varying TiO₂ and SnO₂ concentration;

Figure 5 shows the sensitivity S_{CH4} of oxides of the invention to 1% methane in dry air, at 400°C, with varying TiO₂ and SnO₂ concentration;

Figure 6 shows the sensitivity S_{NH_3} of oxides of the invention to 1% ammonia in dry air, at 400°C, with varying TiO_2 and SnO_2 concentration;

Figure 7 shows the carbon monoxide/methane selectivity in dry air, expressed as Sco/ScH₄, of oxides of the invention, at 400°C, with varying TiO₂ and SnO₂ concentrations;

Figure 8 is similar to Figure 7 but shows the carbon monoxide/ammonia selectivity;

Figure 9 shows the surface cation concentration as a fraction (%) of total surface cation concentration, determined by X-ray photoelectron spectroscopy, for $(FeWO_4)_x(ZO_2)_{1.x}$, with varying TiO_2 and SnO_2 concentrations; and

Figure 10 is similar to Figure 9, but for $(CoWO_4)_x(ZO_2)_{1-x}$. In this specification, gas percentages are by volume.

The wolframites MWO₄ (with M: Mg, Mn, Fe, Co, Ni, Cu and Zn), were prepared by precipitation from aqueous metal nitrate solution by addition of ammonium tungstate solution. The correct preparations were confirmed by X-

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ray powder diffractometry using CuK α radiation (Siemens D5000 in transmission, with incident beam monochromator). The electrical resistivity of these preparations were extremely high R > $10^9~\Omega$.cm at elevated temperature > 500° C). The wolframites were miscible in the solid state with SnO₂ and TiO₂. The complete range of solid solutions (MWO₄)_x([Sn-

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Ti]O₂)_{1-x}, 0<x<1 and M: Mg,Mn, Fe, Co, Ni, Cu and Zn, was successfully prepared by classical solid state synthesis from mixed powders of the tungstate with SnO₂ or TiO₂, with a range of calcination temperature 1000 < T < 1300°C and confirmed by X-ray powder diffraction. Overall, a small quantity (< 5%) of impurity phase content Fe₂WO₆ and Cu₂WO₄ were detected in the FeWO₄- and CuWO₄-substituted materials.

Gas sensitivity and selectivity measurements were studied on compressed, sintered pellets (13mm diameter, \approx 2mm thick) as previously described [3-7]. The electrical resistance of the pellets was first stabilized in dry air at 400°C for 2h. Carbon monoxide, ammonia and methane at low concentration in air were introduced into the rig and the pellet resistance measured at 400 and 500°C. Fig 1 illustrates the typical experimental routine used, and results obtained. Gas sensitivity, S, was calculated as $S = \Delta \sigma/\sigma_o = (R_o - R)/R$, where σ denotes conductivity and R resistance (σ_o , R_o in pure dry air). Hence, a resistance decreasing response is recorded as a positive value and a resistance increasing response as a negative one.

X-ray photoelectron spectroscopy (XPS) was performed (VG ESCALAB 220i XL) using focused (300 μm spot size) monochromatised Al-Kα radiation. The scans were acquired with a step size of 100 meV and the spectrometer pass energy was 20 meV. The binding energies were referenced to the hydrocarbon C 1s peak at 284.80 eV and the sample charging was controlled with a 3 eV flood gun.

The compounds studied covered the range from d^5 to d^{10} with $TiO_2(d^0)$ and $SnO_2(d^{10})$ as end members. Fig 2. shows electrical resistivity as a function of composition at 400° C.

Even small substitutions of Ti or Sn (x = 0.1) brought the resistivity into a measurable

range $(5.10^4 \le \rho \, (\Omega.\text{cm}) \le 2.10^6)$. It is notable that small substitutions of FeWO₄ into either TiO₂ or SnO₂ greatly decreased the resistivity. The behaviour is in contrast to the effect of a direct substitution of Fe, which causes a marked resistivity increase. For small substitutions of NiWO₄ into TiO₂ and SnO₂, the resistivity increased by a factor of two and remained high upon further substitution. Substitutions of the other tungstates gave resistivities clustering in a fairly narrow band well separated from either of these two extremes.

A rough estimate of the activation energies for conduction E_A , was calculated from the resistivities of the materials at 400 and 500°C (Fig 3). Overall, the activation energies were higher for SnO_2 -substituted materials than TiO_2 , which is consistent considering the band gaps of pure TiO_2 and SnO_2 to be respectively, 3.0 eV and 3.6eV. The $NiWO_4$ -and $FeWO_4$ -substituted materials respectively exhibited the highest and lowest activation energy values, which tends to agree with the literature results given in the Introduction. All activation energies for the rest of the substituted materials were clustered between these values. There was an obvious and quite general pattern of variation of E_A with composition for all the compounds: a marked change in activation energy with small substitutions at either end of the series, and a monotonic but relatively small variation with composition between these limits.

Table 1. shows the of resistance changes of $(MWO_4)_x(M'O_2)_{1-x}$ (M = Mn, Fe, Co, Ni, Cu, Zn, and M' = Sn, Ti) upon exposure to wet air, 1% CO, 0.1% NH₃, and 1% CH₄ in air sign ('+' means resistance increase on change of gas from dry to wet air or from dry air to dry air containing the test gas). Table 1 also shows the magnitude of the sensitivity to water vapour, calculated as $|S_{1120}| = |(R_{dry}-R_{wet})/R_{wet}|$, where R_{wet} denotes the resistance in air saturated with water vapour at room temperature ($\approx 20^{\circ}$ C). The reactive gases CO, CH₄ and NH₃ were consistent in their classification of the materials as n- or p-type (figs 4-6, wherein $S_{gas} = (R_0 - R_{gas})/R_{gas}$ meaning that a resistance decrease gives a positive sign for S). However, the sign of response to water vapour was not always consistent. The effect of even small substitutions of the tungstates were greatly to decrease the sensitivity of SnO₂ to water vapour, $|S_{H2O}|$ shifting typically from 1.4 to less than 0.2 for all the tungstates substituted materials. The

magnitude of the response to water vapour varied systematically along the transition series: Mn<Fe,Co<Ni,Cu<Zn. The cases where the sign of the electrical response to water is different to that of the other gases demonstrate that the mechanism of response to water may be different to that of the other gases.

Table 1. Sign of resistance changes of $(MWO_4)_x(M'O_2)_{1-x}$ (M = Mn, Fe, Co, Ni, Cu, Zn, and M' = Sn, Ti) upon exposure to wet air, 1% CO, 0.1% NH_3 , and 1% CH_4 in air ('+' means resistance increase on change of gas from dry to wet air or from dry air to dry air containing the test gas). and sensitivity to water vapour $|S_{H2O}| = |(R_{dry}-R_{wet})/R_{wet}|$ $(dry \rightarrow 100\%$ RH at $20^{\circ}C$).

		TiO ₂		-		X _w	dframite		→		SnO ₂
		0.1	0.3	0.7	0.9	1	0.9	0.7	0.5	0.3	0.1
Mn	gas	-	+	+	+		+	+	-	-	-
•	H ₂ O S _{H2O} = 0.04±0.03	-	-	-	-		-	-	-	-	-
Fe	gas	-	_	-	+		+	-	-	_	_
	H ₂ O S _{H2O} =0.1±0.07	-	-	+	+		+	+	+	+	-
Co	gas	-	-	+	+		+	+	+	-	-
	H ₂ O S _{H2O} =0.11±0.06	-	-	+	+		+	+	+	-	-
Ni	gas	_	-	-	-		-	_	_	-	_
	H ₂ O S _{H2O} =0.2±0.1	-	-	+	+		+	+	+	-	-
Cu	gas	1-	-	_	_		-	-	-	-	-
	H ₂ O S _{H2O} =0.2±0.1	-	-	-	•		-	-	-	-	-
Zn	gas	_	+	+	+		+	-	_	_	-
	H ₂ O S _{H2O} =0.44±0.2	-	+	+	+		+	+	-	-	-
		iO ₂						Sn	O_2		
gas					_						
H ₂ O	· · · · · · · · · · · · · · · · · · ·	1				_					
$S_{\rm HZO}$			0.:	2					.4		

Several points are worth noting concerning the effect of composition on sensitivity. As expected, a notable feature is that, with change in composition along both series, the behaviour for some materials changes from 'n-type' (resistance decrease in the presence of the reducing gas) to 'p-type' (gas causes a resistance increase). Only the Ni- and Cu-based materials remained n-type along both series (SnO₂ and TiO₂). These two sets of materials did show a minimum in sensitivity across the range. For the Ni series, the minimum was on the TiO2 side, whereas for the Cu series it was on the SnO₂ side. The n-type compounds exhibited much higher sensitivity to CO than the ptype materials but for CH4, the differences between n- and p-type materials were not so marked. The Co series was notable in showing a rather strong p-type sensitivity to CH₄ on the SnO₂ branch, just before the n-p transition. The n-p transition was found over the same composition range for all the reactive gases. Considering the mole fraction of tungstate, y, at which the n-p transition takes place, the sequence along the TiO₂ branch is Zn < Mn, Co < Fe and along the SnO₂ branch is Co < Mn < Zn, Fe, so the zinc compound was notable in showing asymmetrical behaviour with respect to the two end members. There was a remarkable maximum in the sensitivity to CO at y =0.3 - 0.5 along the SnO₂ branch, for the Fe, Ni, Cu and Zn series, but not for the Mn or Co series. Any such maximum along the TiO₂ branch was not nearly so marked. For sensitivity to methane, a similar maximum was observed, but only for the Ni series. The Ni series on the SnO₂ side was interesting because small substitutions produced a decrease in sensitivity to both CO and CH4 then further substitution caused a marked increase in sensitivity (n-type) to the maximum.

The carbon monoxide-methane selectivity of all the compounds determined at 400°C is given in Fig 7, and the carbon monoxide-ammonia selectivity with the Mn, Fe and Zn compounds in Fig 8. The Mn, Co, Ni and Cu compounds showed a very stable CO/CH₄ selectivity along both branches (Fig 7) varying from 1 for Mn to 5 for Cu. For Fe and Zn the selectivity remained stable along the TiO₂ branch, but then went through a strong maximum along the SnO₂ branch, increasing by a factor up to 10. The Mn and Fe compounds showed a stable CO/NH₃ selectivity (0 < S_{CO} / S_{NH3} < 1) along both series. The Zn compounds however exhibited a different behavior with a high selectivity (up to 7) along the TiO₂ branch (Fig 8).

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Fig. 9 and 10 give the surface concentration (atom%) vs. TiO₂ and SnO₂ mole ratio obtained by XPS surface analysis for the Fe- and Co-based materials. It is quite clear from these diagrams that the switch from n-type to p-type gas sensitivity appeared to occur when the surface concentration of Ti and Sn started to decrease significantly. For both series there was a clear segregation of W to the surface corresponding to the suppression of the other cation, particularly the transition metal cation. This segregation was not found for the pure MWO₄. Titanium seemed to be present at the surface more or less in the concentration expected from the bulk composition. In the n-type range, Sn was repelled from the surface in the Fe-series; the effect was not so marked in the Co-series.

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CLAIMS:-

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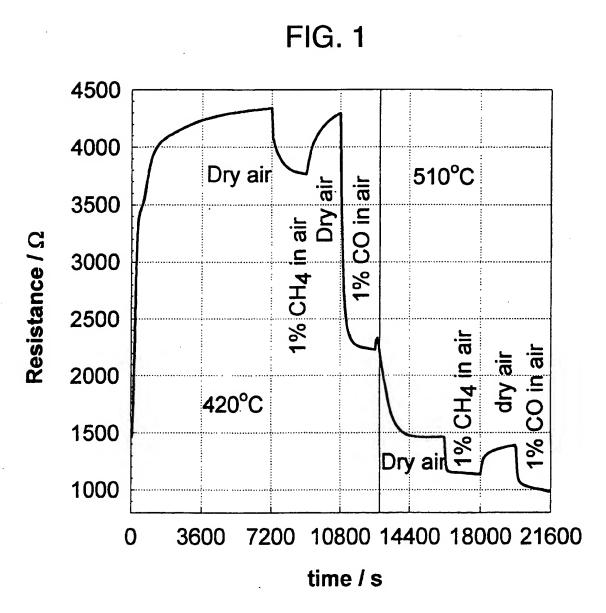
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1. A compound of the formula:

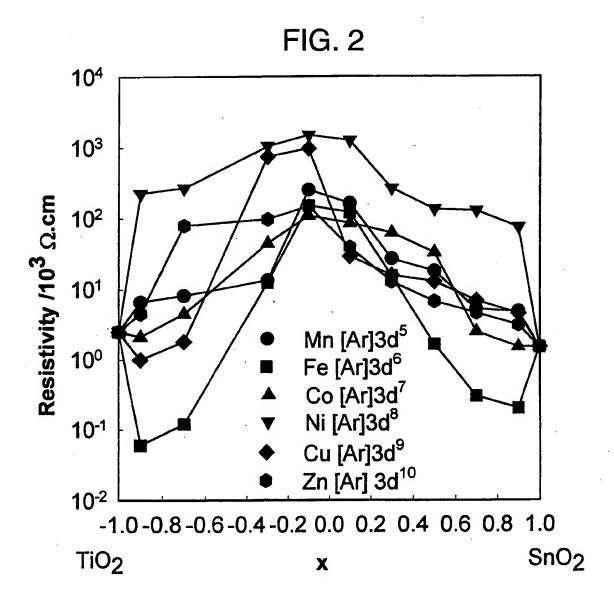
 $(MWO_4)_x(ZO_2)_{1-x}$

where M is selected from Mg, Mn, Fe, Co, Ni, Cu, and/or Zn, and Z is selected from Sn and Ti, where 0 < x < 1.

- 2. A compound according to claim 1 when in the form of a wolframite-based solid solution.
- 3. A compound according to claim 1 or 2 wherein M is a single one of Mg, Mn, Fe, Co, Ni, Cu or Zn.
- 4. A compound according to any preceding claim wherein Z is a single one of Sn or Ti.
 - 5. A gas sensor having at least one pair of electrodes in contact with a compound as claimed in any of claims 1 to 3.
 - A gas sensor according to claim 5 wherein the compound is disposed as a film on an inert substrate.
 - 7. A gas sensor according to claim 5 or 6 wherein the film is up to 300 microns thick.
 - 8. Use of a gas sensor according to any of claims 5 to 7 for detecting, or measuring the concentration of a gas in a gas mixture.
- Use of a gas sensor according to claim 8 wherein the gas is carbon monoxide, methane or ammonia.
 - 10. Use of a gas sensor according to claim 8 wherein the gas mixture contains air.



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FIG. 3

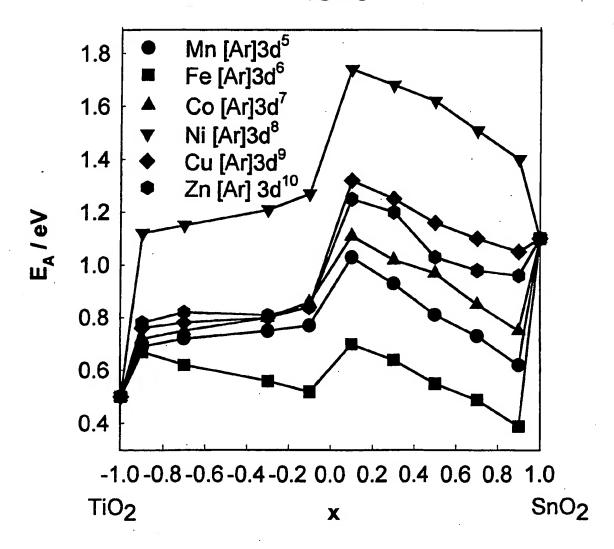
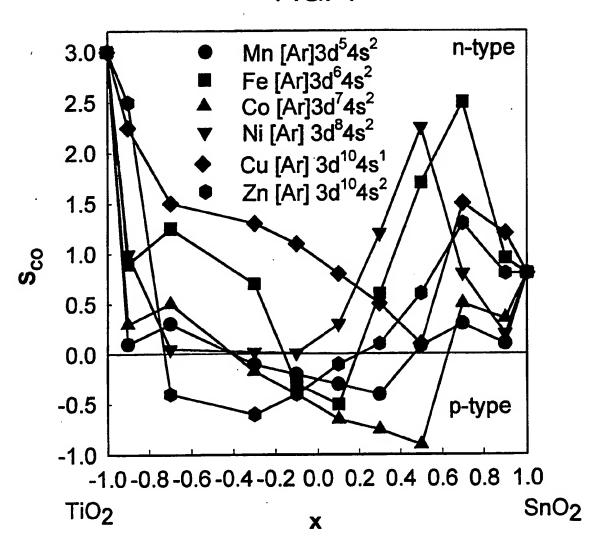
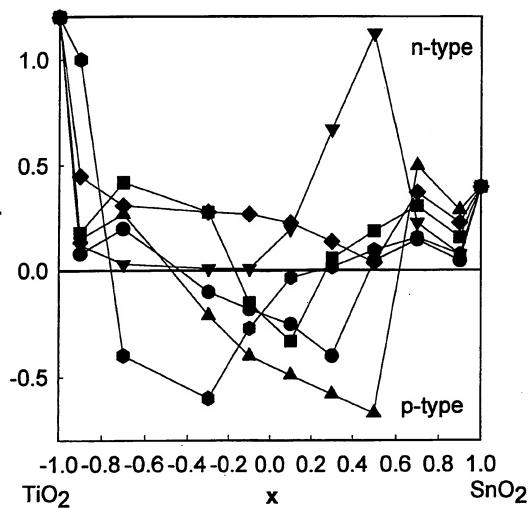


FIG. 4

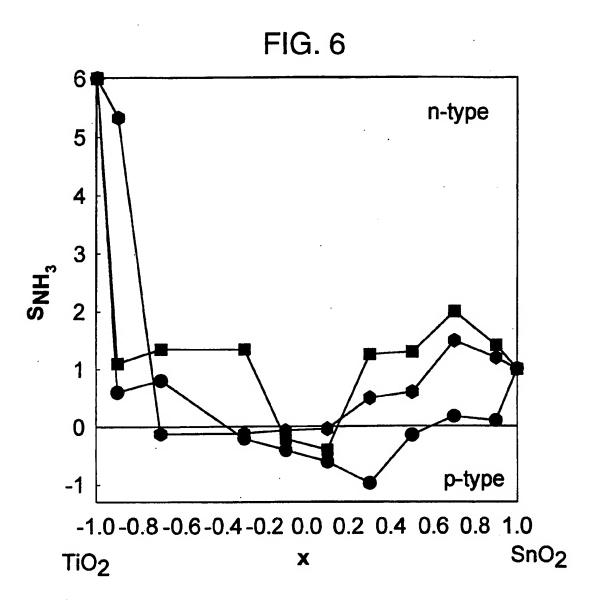




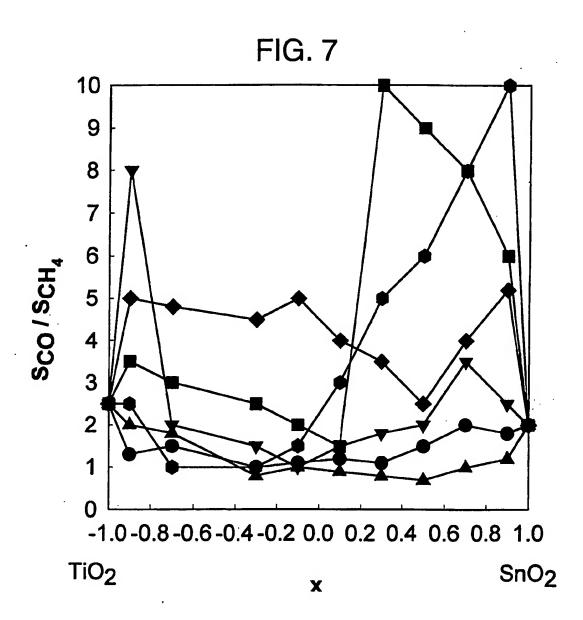


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- Mn [Ar]3d⁵4s²
 Fe [Ar]3d⁶4s²
 Co [Ar]3d⁷4s²
 Ni [Ar] 3d⁸4s²
 Cu [Ar] 3d¹⁰4s¹
 Zn [Ar] 3d¹⁰4s²

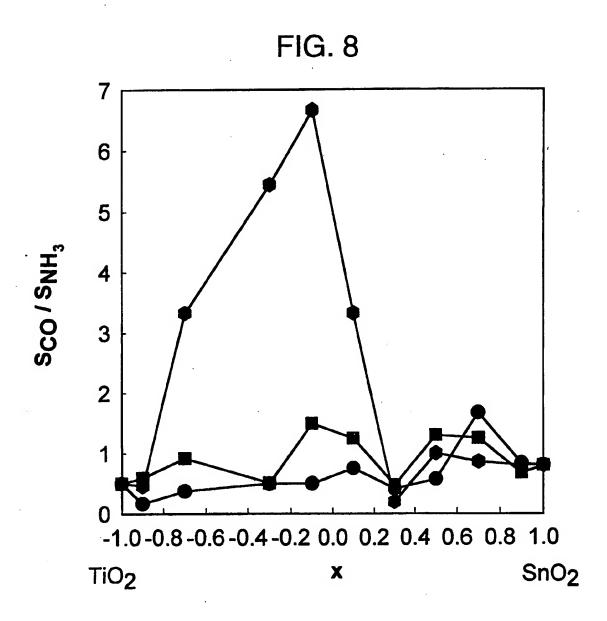


- Mn [Ar]3d⁵4s² Fe [Ar]3d⁶4s² Zn [Ar]3d¹⁰4s²



- Mn [Ar]3d⁵4s² Fe [Ar]3d⁶4s² Co [Ar]3d⁷4s² Ni [Ar] 3d⁸4s²

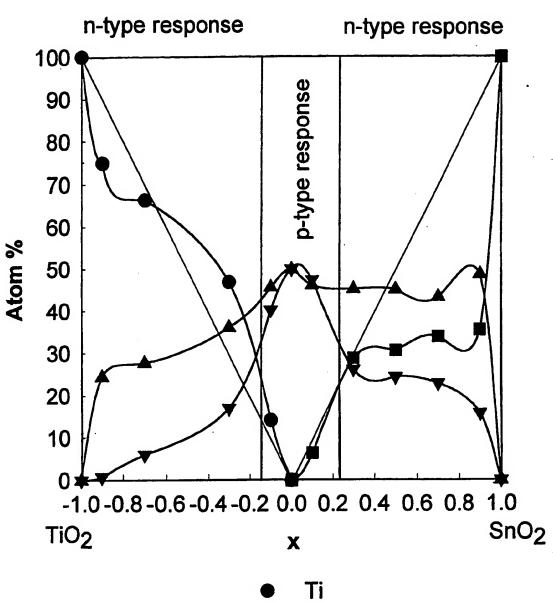
- Cu [Ar] 3d¹⁰4s¹
- Zn [Ar] 3d¹⁰4s²



- Mn [Ar]3d⁵4s² Fe [Ar]3d⁶4s²
- Zn [Ar] 3d¹⁰4s²

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FIG. 9

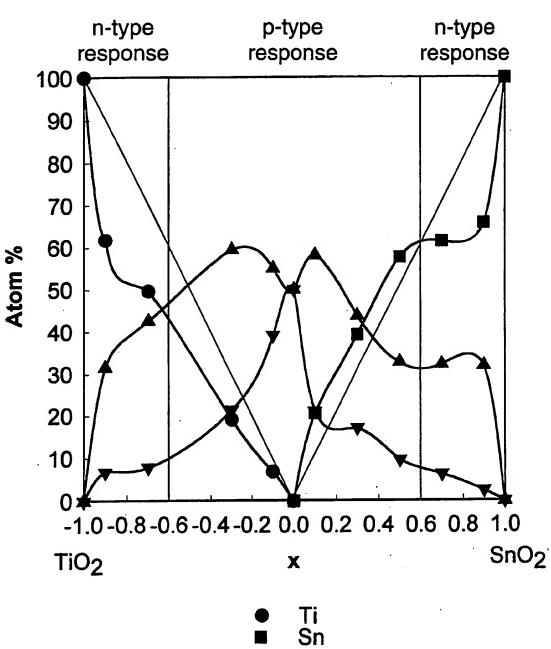


Sn

W

Fe

FIG. 10



W Co

INTERNATIONAL SEARCH REPORT

Inter one Application No PCT/GB 99/03160

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Electronic d	ists bese consulted during the international search (name of d	ata base and, where practical, sea	rch terms used)
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	Europeen Patent Office, P.B. 6816 Patentiaan 2 NL – 2280 HV Rijenijk Tel. (+31–70) 340–2040, Tx. 31 651 epo ni, Fax: (+31–70) 340–3018	Duchate11	•
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